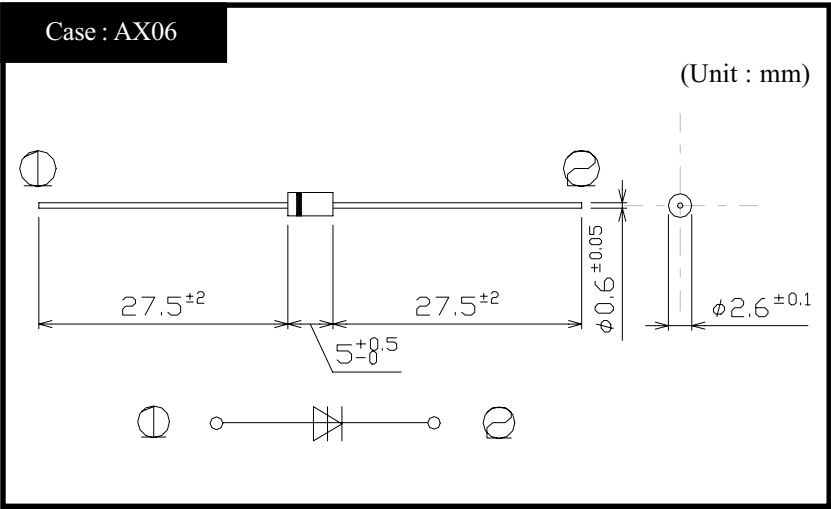


G1V(A)8C

OUTLINE DIMENSIONS



RATINGS

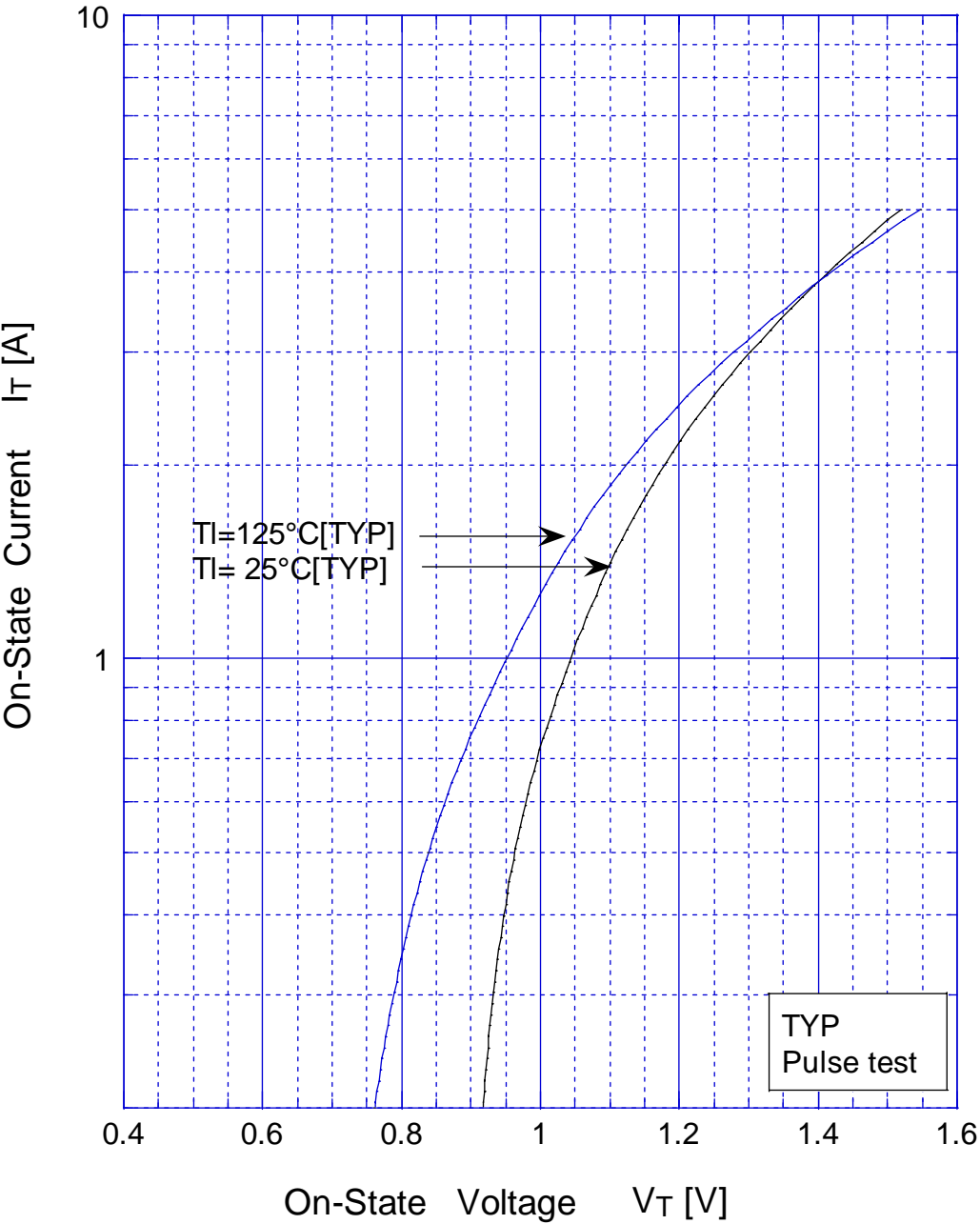
Absolute Maximum Ratings (Unless otherwise specified, Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-40~125	°C
Operating Junction Temperature	Tj		125	°C
Maximum Off-state Voltage	V <sub>DRM(A)</sub>		70	V
RMS On-state Current	I <sub>T</sub>	Tl = 98°C, 50Hz Sine wave ( θ = 180°)	1	A
Pulse On-state Current	I <sub>TRM</sub>	Ta = 25 °C, Pulse width 10 μ s, 60 Hz Sine wave	80	A
Critical Rate of Rise of On-state Current	di <sub>T</sub> /dt		80	A/ μ s

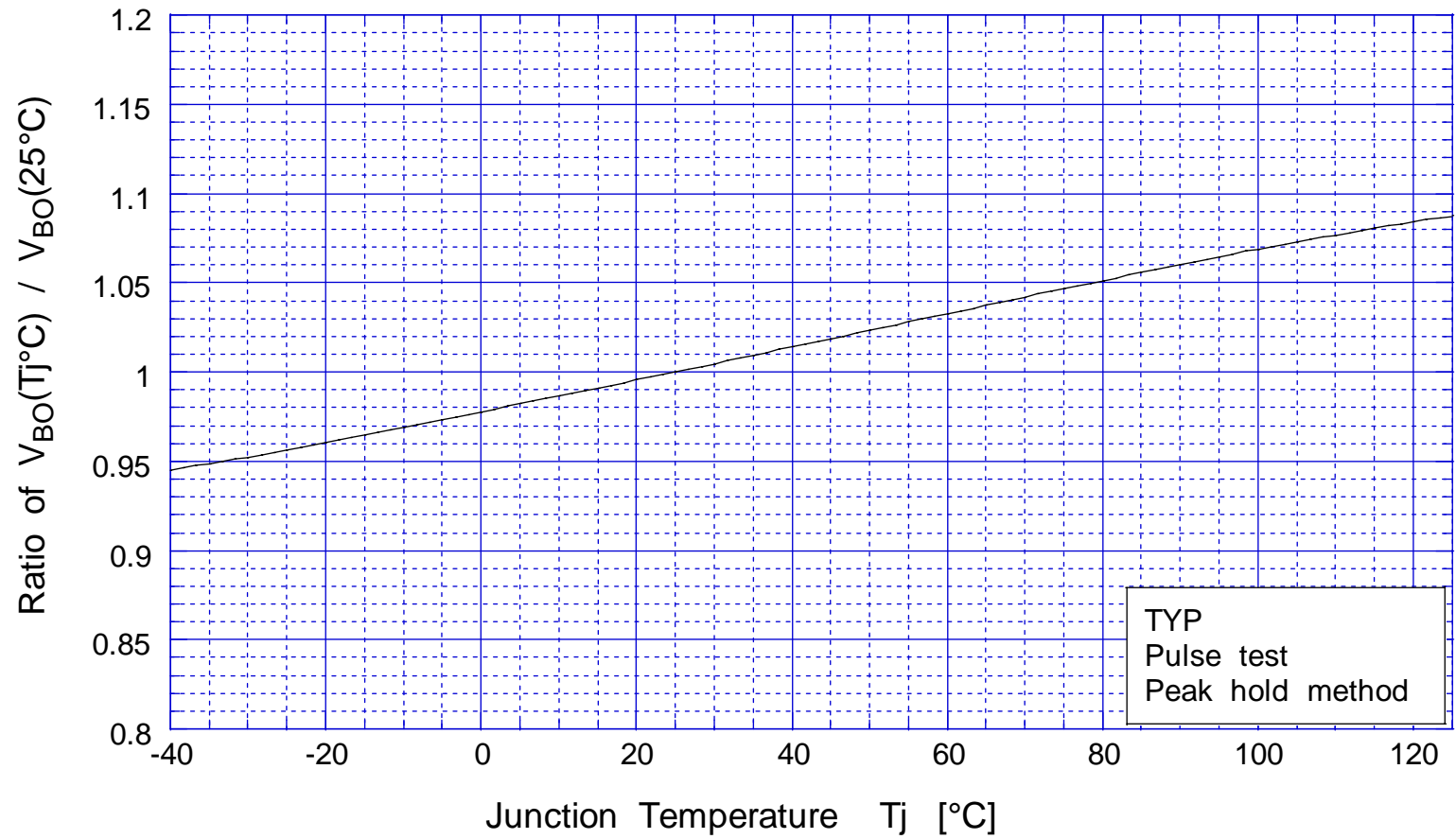
Electrical Characteristics (Unless otherwise specified, Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V <sub>BO(A)</sub>	Pulse measurement (dv/dt = 4V/ms)	Min 75 Max 90	V
Off-state Current	I <sub>DRM(A)</sub>	V <sub>D</sub> = V <sub>DRM(A)</sub>	Max 10	μ A
Breakover Current	I <sub>BO(A)</sub>		Max 1.0	mA
Holding Current	I <sub>H(A)</sub>		Max 60	mA
	I <sub>H(K)</sub>			
On-state Voltage	V <sub>T(A)</sub>	I <sub>T</sub> = 1A	Max 1.5	V
	V <sub>T(K)</sub>	I <sub>T</sub> = 1A		
Switching Resistance	R <sub>S(A)</sub>		Min 0.1	k Ω
Thermal Resistance	θ jl	Junction to lead	Max 20	°C/W

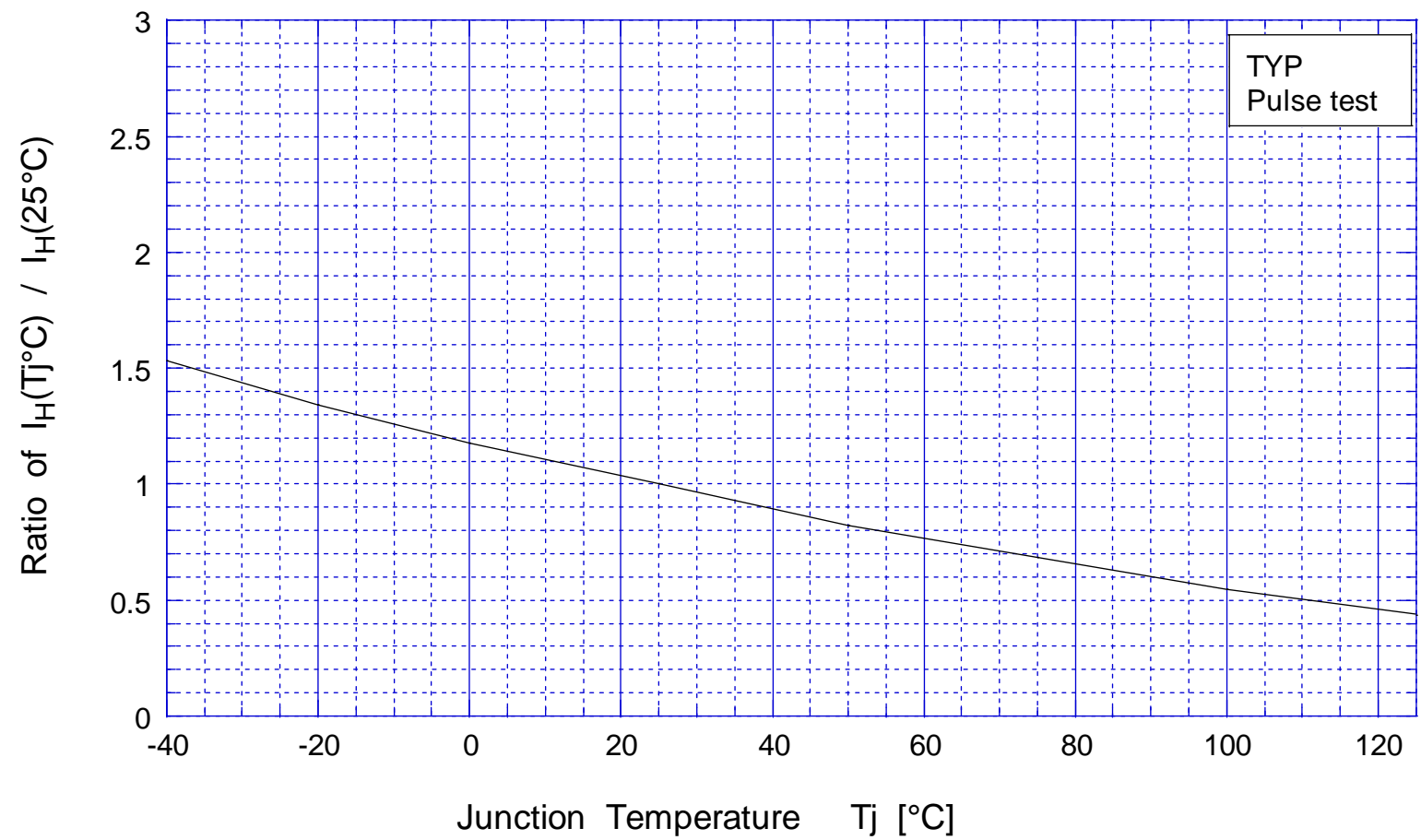
G1V(A)8C On-State Voltage - On-State Current



## G1V(A)8C Break Over Voltage - Junction Temperature



## G1V(A)8C Holding Current - Junction Temperature



## G1V(A)8C Pulse On-state Current Rating

